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Supplementary information

Time-difference blow-spinning to a flexible dual-scale multilayer fabric for high-efficient electromagnetic interference shielding

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Supplementary Text

Statistics of MLPAN layer spacing

In order to measure the layer spacing of MLPAN, we collected 60-point data from cross-section SEM images at random positions, results are shown in Fig. S2. It is found that the layer spacing of MLPAN is mainly distributed in \sim 20 μ m when the rotating speed was set as 2 degree per second.

XPS peak differentiation imitating analysis

XPS spectra peak differentiation imitating of Ti 2p and C 1s core levels of $Ti_3C_2T_x$ and $Ti_3C_2T_x/MLPAN$ are shown in Fig. 2f and S7, details of binding energy are shown in Table S2. Ti 2p core level for both of them can be assigned into four doublets (Ti $2p_{3/2}$ -Ti $2p_{1/2}$).⁶⁶ In the $Ti_3C_2T_x$, the C 1s core level can be fitted with six components centered at 291.4, 288.7, 286.2, 284.8, 282.3 and 281.8 eV, which can be assigned to π - π *, O-C=O, C-O, C-C, Ti-C-O and C-Ti bonds, respectively.^{66,67} C 1s peak differentiation imitating for $Ti_3C_2T_x/MLPAN$ distributed into seven components centered at 291.4, 288.7, 286.6, 286.2, 284.8, 282.3 and 281.8 eV, which can be assigned to π - π * hybridization, O-C=O, C=N, C-O, C-C, Ti-C-O and C-Ti bonds, respectively.⁶⁶⁻⁶⁸

Electrical characteristics

IV/CV probe installation was used to measure the electrical characteristics of $Ti_3C_2T_x/MLPAN$. The conductivity and sheet resistance of materials can be calculated as follows:

$$\sigma = \frac{l}{RS} \#(S1)$$

$$R_{S} = \frac{1}{\sigma t} \#(S2)$$

Electromagnetic interference (EMI) shielding characteristics

EMI shielding characteristics of as-prepared samples were measured via a 2-port vector network analyzer (PNA-L N5230C, Agilent Technologies, USA) with 8.2 to 12.4 GHz calibration kit. Before testing, all samples were cut into modular size (24 mm × 12 mm) and fixed in a square hollow waveguide (22.84 mm × 10.14 mm). Electromagnetic interference shielding effectiveness (EMI SE) in decibels (dB) can be defined as:^{69,70}

$$SE(dB) = 10log\left(\frac{P_i}{P_t}\right) \#(S3)$$

where $^{P_{i}}$ and $^{P_{t}}$ are the power of incident wave and transmitted wave, respectively. The total SE (SE_{Total}) is defined as the sum of three terms include reflection loss (SE_R), absorption loss (SE_A), and multiple internal reflection loss (SE_M).⁷¹ Particularly, SE_M for multilayer materials can be merged in the absorption loss due to the absorbed or dissipated of incident electromagnetic wave occurred in the shielding material.³¹ Equation 6 and 7 in main text can also be derived from power coefficients relation as follows:

$$SE_R = 10log(\frac{1}{1-R})\#(S4)$$

$$SE_A = 10log(\frac{1-R}{T}) \#(S5)$$

wherein, R is reflectivity and T is transmissivity. The corresponding power coefficients of R, T and absorptivity (A) follow the law of power balance:

$$R + T + A = 1\#(S6)$$

The relations between power coefficients and S-parameters can be described as:

$$R = |S_{11}|^2 \# (S7)$$

$$T = |S_{21}|^2 \# (S8)$$

According to equation 10 in main text, defining Δ as the difference between the denominator and the numerator of the attenuation coefficient β , which is equal to:

$$\Delta = 1 + (e^{-\gamma t} - e^{-2\gamma t})\Gamma_1^2 - e^{-\gamma t} \#(S9)$$

wherein, considering that $\gamma t > 0$, $(e^{-\gamma t} - e^{-2\gamma t})$ is always greater than 0 and $e^{-\gamma t}$ is always less than 1. It can be seen that Δ is always greater than 0, and the attenuation coefficient β between 0 and 1, indicating the incident electromagnetic wave decays exponentially in conduction process.

CST electromagnetic simulations

Electromagnetic simulations were performed in computer simulation technology microwave studio (CST MWS 2019) based on a four-layer sandwich structure approximate model as shown in Fig. S21. The model consists two kinds of structures: the external high conductivity part ($Z_{\rm I}$) and the internal low conductivity part ($Z_{\rm IV}$), corresponding to different content of Ti₃C₂T_x deposited on bilateral, and permeated inside. The material type of Ti₃C₂T_x is

set to ohmic sheet, and the sheet resistances of the two parts for different $Ti_3C_2T_x$ content samples are respectively set to:

38.3 wt.%:
$$Z_{\rm I}$$
 = 2.25 Ω sq⁻¹ and $Z_{\rm IV}$ = 1350.00 Ω sq⁻¹;
49.6 wt.%: $Z_{\rm I}$ = 1.72 Ω sq⁻¹ and $Z_{\rm IV}$ = 1025.00 Ω sq⁻¹;
58.4 wt.%: $Z_{\rm I}$ = 0.58 Ω sq⁻¹ and $Z_{\rm IV}$ = 712.00 Ω sq⁻¹;
63.6 wt.%: $Z_{\rm I}$ = 0.38 Ω sq⁻¹ and $Z_{\rm IV}$ = 520.00 Ω sq⁻¹

according to the test results. The electromagnetic characteristics of PAN layer ($Z_{\rm II}$) and the gaps ($Z_{\rm III}$) are both considered the same as air due to the aerogel-like structure of PAN. In this simulation, square hollow waveguide size conforms to its real size, and the electromagnetic waves travel in the negative direction of the Z-axis with the frequency of 8 to 12 GHz. All simulations were performed in time domain.



Fig. S1. High speed camera image of nozzle during time-difference blow-spinning.

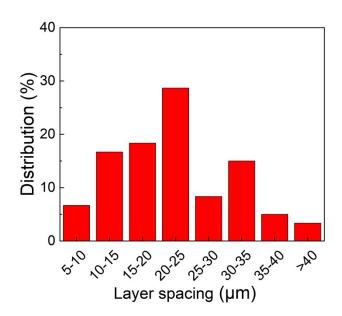


Fig. S2. Distribution of layer spacing of MLPAN measured by 60-point cross-section SEM images.

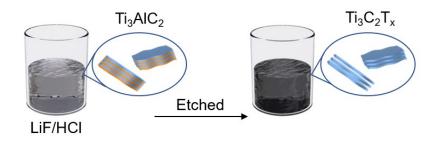


Fig. S3. The preparation process of $Ti_3C_2T_x$ by etching Ti_3AlC_2 in LiF/HCl.

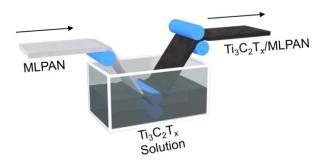


Fig. S4. A typical solution dip-coating process for conducting modification of MLPAN by $Ti_3C_2T_x.$



Fig. S5. Photographs of a flexible $Ti_3C_2T_x/MLPAN$ hybrid fabric.

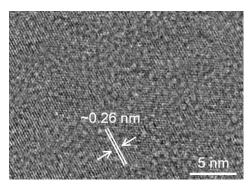


Fig. S6. HR-TEM image of a monolayer $Ti_3C_2T_x$ nanosheet.

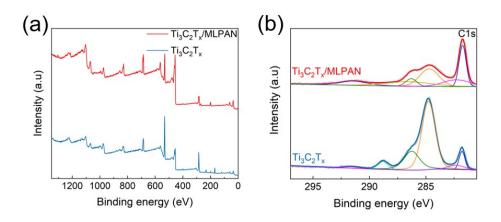


Fig. S7. XPS results of $Ti_3C_2T_x$ and $Ti_3C_2T_x/MLPAN$ include (a) survey, and (b) peak differentiation imitating analysis of C1s.

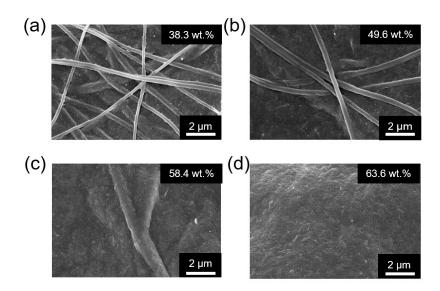


Fig. S8. Zoom-in surface SEM images of $Ti_3C_2T_x/MLPAN$ with different $Ti_3C_2T_x$ content of (a) 38 ° 2 wt.%, (b) 49.6 wt.%, (c) 58.4 wt.% and (d) 63.6 wt.%.

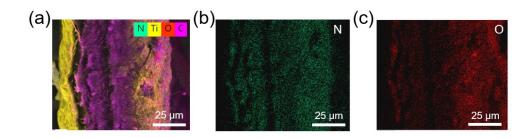


Fig. S9. Cross-section EDS elemental mapping results of $Ti_3C_2T_x/MLPAN$ include (a) survey, (b) N, and (c) O.

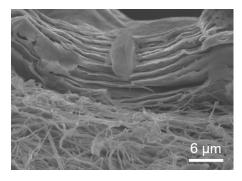


Fig. S10. Cross-section SEM image of $Ti_3C_2T_x/MLPAN$ around compound interface.

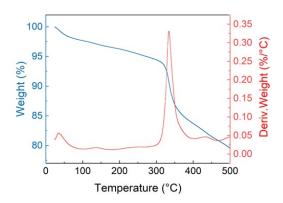


Fig. S11. TGA (blue) and DTG (red) of $Ti_3C_2T_x/MLPAN$.

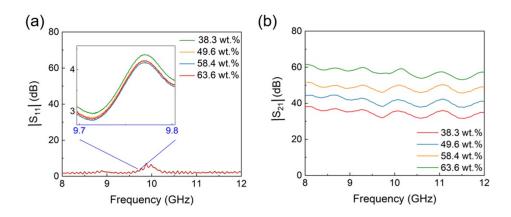


Fig. S12. S-parameters include (a) $|S_{11}|$ and (b) $|S_{21}|$ of $Ti_3C_2T_x/MLPAN$ with different $Ti_3C_2T_x$ content of 38.3 wt.%, 49.6 wt.%, 58.4 wt.% and 63.6 wt.%.

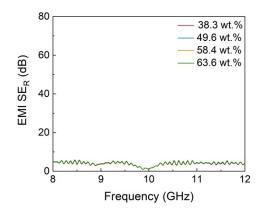


Fig. S13. SE_R of $Ti_3C_2T_x/MLPAN$ with different $Ti_3C_2T_x$ content of 38.3 wt.%, 49.6 wt.%, 58.4 wt.% and 63.6 wt.%.

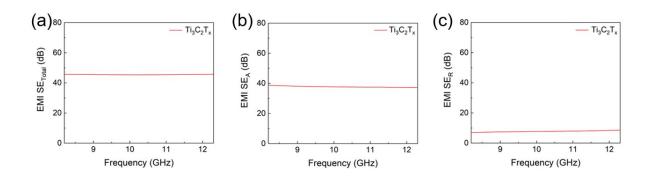


Fig. S14. EMI SE of $Ti_3C_2T_x$ extraction film, (a) EMI SE_{Total}, (b) EMI SE_A, (c) EMI SE_R. The $Ti_3C_2T_x$ thin-film mass was approximately 4.4 mg. In the $Ti_3C_2T_x$ /MLPAN with a $Ti_3C_2T_x$ content of 63.6 wt.%, the $Ti_3C_2T_x$ mass used was approximately 4.3 mg.

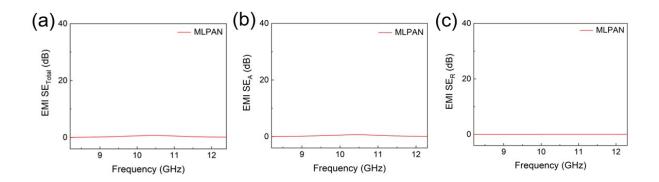


Fig. S15. EMI SE of MLPAN include (a) EMI SE_{Total} , (b) EMI SE_A , and (c) EMI SE_R .

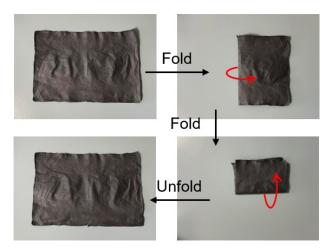


Fig. S16. Folding demonstration of as-prepared $Ti_3C_2T_x/MLPAN$ hybrid fabric.



Fig. S17. Coiling demonstration of as-prepared $Ti_3C_2T_x/MLPAN$ hybrid fabric.

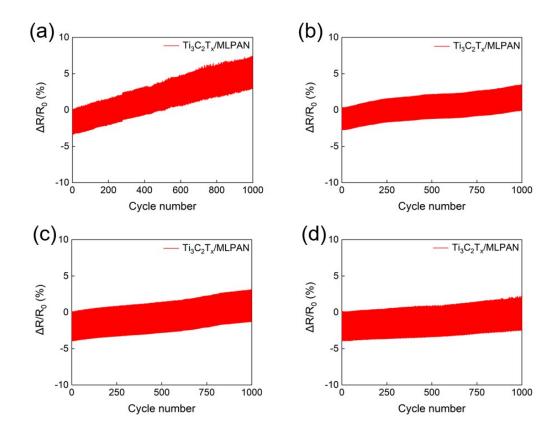


Fig. S18. Real-time resistance changes of $Ti_3C_2T_x$ /MLPAN with different $Ti_3C_2T_x$ content of (a) 38.3 wt.%, (b) 49.6 wt.%, (c) 58.4 wt.% and (d) 63.6 wt.% during 1000-cycle bending.

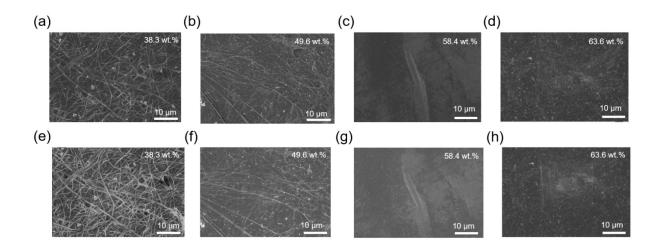


Fig. S19. SEM images of $Ti_3C_2T_x/MLPAN$ with different $Ti_3C_2T_x$ content of 38.3 wt.%, 49.6 wt.%, 58.4 wt.% and 63.6 wt.% before (a-d) and after (e-h) 1000-cycles of bending.

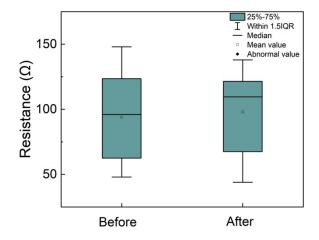


Fig. S20. Resistance of $Ti_3C_2T_x/MLPAN$ film before and after soaking in water for 24-hour.

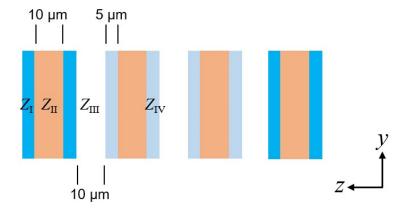


Fig. S21. Structure schematic diagram in CST simulation. X axial and Y axial scales of the structure follow the actual size of 8-12 GHz rectangular wave guide.



Fig. S22. Top view of electric field simulation result, wherein the incident wave propagates in the negative Z-axis direction.

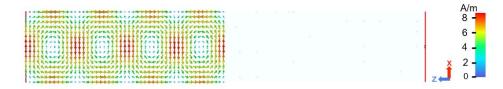


Fig. S23. Top view of magnetic field simulation result, wherein the incident wave propagates in the negative Z-axis direction.

Table S1. SE_{Total} and power coefficient of MLPAN, $Ti_3C_2T_x$, and $Ti_3C_2T_x$ /MLPAN with different $Ti_3C_2T_x$ content.

Materials	Ti ₃ C ₂ T _x Content [wt.%]	SE _{Total} [dB]	R	A	Т
MLPAN	-	5.0×10^{-2}	0.001	0.010	0.988
Ti ₃ C ₂ T _x /MLPAN	38.3	38.2	0.665	0.334	1.510×10 ⁻⁴
Ti ₃ C ₂ T _x /MLPAN	49.6	44.4	0.671	0.328	3.500×10 ⁻⁵
Ti ₃ C ₂ T _x /MLPAN	58.4	51.7	0.679	0.320	6.492×10 ⁻⁶
Ti ₃ C ₂ T _x /MLPAN	63.6	61.8	0.681	0.318	6.489×10 ⁻⁷
$Ti_3C_2T_x$	100.0	45.5	0.818	0.181	2.798×10 ⁻⁵

Table S2. Details of XPS peak differentiation imitating analysis.

Region	BE (eV)	Assigned to
Ti 2p _{3/2} (2p _{1/2})	455 (461.2)	C-Ti-(O/OH)
	455.8 (461.3)	C-Ti ²⁺ -(O/OH)
	458.6 (464.2)	TiO_2
	459.3 (465.3)	$TiO_{2\text{-}x}F_{2x}$
Cls	281.8	C-Ti
	282.3	Ti-C-O
	284.8	С-С
	286.2	С-О
	288.7	O-C=O
	291.4	π - π *
	286.6	C≡N

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